

DISCRETE SEMICONDUCTORS

DATA SHEET

BUW11F; BUW11AF Silicon diffused power transistors

Product specification
Supersedes data of February 1996
File under Discrete Semiconductors, SC06

1997 Aug 14

Silicon diffused power transistors

BUW11F; BUW11AF

DESCRIPTION

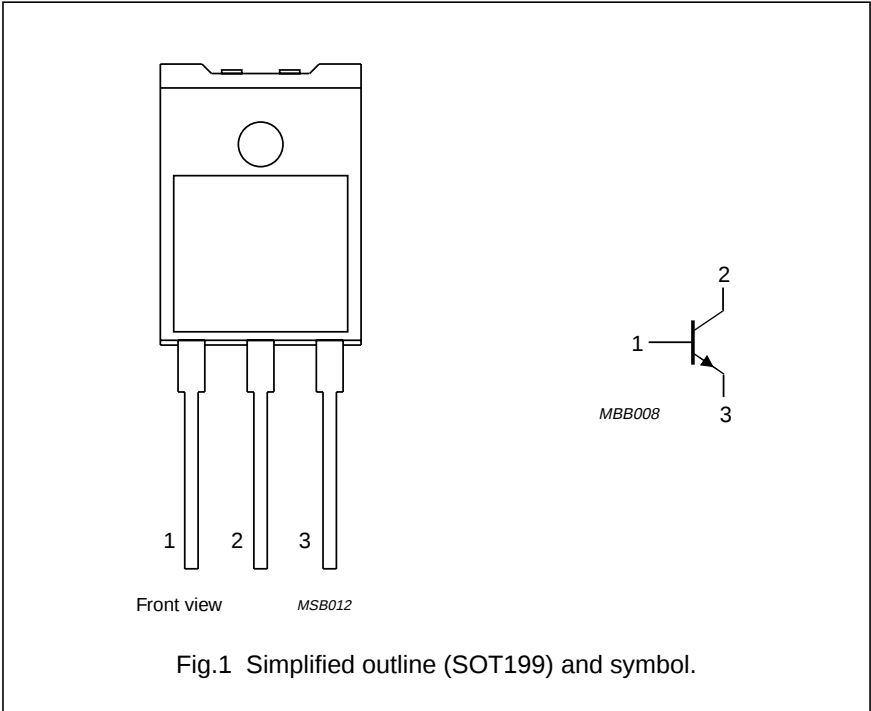
High-voltage, high-speed, glass-passivated NPN power transistor in a SOT199 package.

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor control systems.

PINNING

PIN	DESCRIPTION
1	base
2	collector
3	emitter
mb	mounting base; electrically isolated



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0$		
	BUW11F		850	V
	BUW11AF		1000	V
V_{CEO}	collector-emitter voltage	open base		
	BUW11F		400	V
	BUW11AF		450	V
V_{CEsat}	collector-emitter saturation voltage		1.5	V
I_{Csat}	collector saturation current			
	BUW11F		3	A
	BUW11AF		2.5	A
I_C	collector current (DC)	see Figs 2 and 4	5	A
I_{CM}	collector current (peak value)	$t_p < 20\text{ ms}$; see Fig.2	10	A
P_{tot}	total power dissipation	$T_h \leq 25\text{ }^\circ\text{C}$; see Fig.3	32	W
t_f	fall time	resistive load; see Figs 8 and 9	0.8	μs

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-h}$	thermal resistance from junction to external heatsink	note 1	3.95	K/W
		note 2	3.05	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient		35	K/W

Notes

1. Mounted **without** heatsink compound and 30 ± 5 N force on centre of package.
2. Mounted **with** heatsink compound and 30 ± 5 N force on centre of package.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	collector-emitter peak voltage BUW11F BUW11AF	$V_{BE} = 0$	—	850	V
			—	1000	V
V_{CEO}	collector-emitter voltage BUW11F BUW11AF	open base	—	400	V
			—	450	V
I_{Csat}	collector saturation current BUW11F BUW11AF		—	3	A
			—	2.5	A
I_C	collector current (DC)	see Figs 2 and 4	—	5	A
I_{CM}	collector current (peak value)	$t_p < 20$ ms; see Fig.2	—	10	A
I_B	base current (DC)		—	2	A
I_{BM}	base current (peak value)	$t_p < 20$ ms	—	4	A
P_{tot}	total power dissipation	$T_h \leq 25$ °C; see Fig.3; note 1	—	32	W
		$T_h \leq 25$ °C; see Fig.3; note 2	—	41	W
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C

Notes

1. Mounted **without** heatsink compound and 30 ± 5 N force on centre of package.
2. Mounted **with** heatsink compound and 30 ± 5 N force on centre of package.

ISOLATION CHARACTERISTICS

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{isolM}	isolation voltage from all terminals to external heatsink (peak value)	—	1500	V
C_{isol}	isolation capacitance from collector to external heatsink	—	21	pF

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CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

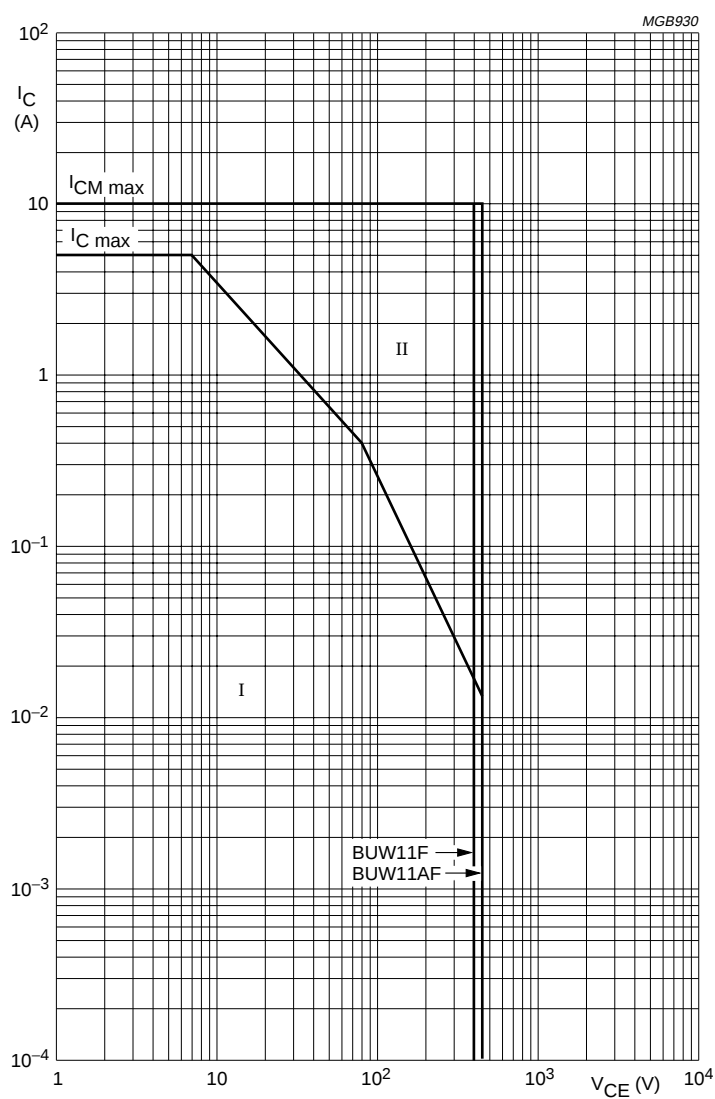
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CEOsust}$	collector-emitter sustaining voltage BUW11F BUW11AF	$I_C = 100\text{ mA}$; $I_{Boff} = 0$; $L = 25\text{ mH}$; see Figs 5 and 6	400 450	— —	— —	V V
V_{CEsat}	collector-emitter saturation voltage BUW11F BUW11AF	$I_C = 3\text{ A}$; $I_B = 600\text{ mA}$	—	—	1.5	V
		$I_C = 2.5\text{ A}$; $I_B = 500\text{ mA}$	—	—	1.5	V
V_{BEsat}	base-emitter saturation voltage BUW11F BUW11AF	$I_C = 3\text{ A}$; $I_B = 600\text{ mA}$	—	—	1.4	V
		$I_C = 2.5\text{ A}$; $I_B = 500\text{ mA}$	—	—	1.4	V
I_{Csat}	collector saturation current BUW11F BUW11AF	$V_{CE} = 1.5\text{ V}$	— —	— —	3 2.5	A A
I_{CES}	collector-emitter cut-off current	$V_{CE} = V_{CESMmax}$; $V_{BE} = 0$; note 1	—	—	1	mA
		$V_{CE} = V_{CESMmax}$; $V_{BE} = 0$; $T_j = 125\text{ °C}$; note 1	—	—	2	mA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 9\text{ V}$; $I_C = 0$	—	—	10	mA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}$; $I_C = 5\text{ mA}$; see Fig.7	10	18	35	
		$V_{CE} = 5\text{ V}$; $I_C = 0.5\text{ A}$; see Fig.7	10	20	35	
Switching times resistive load (Figs 8 and 9)						
t_{on}	turn-on time BUW11F BUW11AF	$I_{Con} = 3\text{ A}$; $I_{Bon} = -I_{Boff} = 600\text{ mA}$	—	—	1	μs
		$I_{Con} = 2.5\text{ A}$; $I_{Bon} = -I_{Boff} = 500\text{ mA}$	—	—	1	μs
t_s	storage time BUW11F BUW11AF	$I_{Con} = 3\text{ A}$; $I_{Bon} = -I_{Boff} = 600\text{ mA}$	—	—	4	μs
		$I_{Con} = 2.5\text{ A}$; $I_{Bon} = -I_{Boff} = 500\text{ mA}$	—	—	4	μs
t_f	fall time BUW11F BUW11AF	$I_{Con} = 3\text{ A}$; $I_{Bon} = -I_{Boff} = 600\text{ mA}$	—	—	0.8	μs
		$I_{Con} = 2.5\text{ A}$; $I_{Bon} = -I_{Boff} = 500\text{ mA}$	—	—	0.8	μs
Switching times inductive load (Figs 10 and 11)						
t_s	storage time BUW11F	$I_{Con} = 3\text{ A}$; $I_B = 600\text{ mA}$; $V_{CL} = 250\text{ V}$; $T_c = 100\text{ °C}$	—	2	2.5	μs
	BUW11AF	$I_{Con} = 2.5\text{ A}$; $I_B = 500\text{ mA}$; $V_{CL} = 300\text{ V}$; $T_c = 100\text{ °C}$	—	2	2.5	μs
t_f	fall time BUW11F	$I_{Con} = 3\text{ A}$; $I_B = 600\text{ mA}$; $V_{CL} = 250\text{ V}$; $T_c = 100\text{ °C}$	—	200	300	ns
	BUW11AF	$I_{Con} = 2.5\text{ A}$; $I_B = 500\text{ mA}$; $V_{CL} = 300\text{ V}$; $T_c = 100\text{ °C}$	—	200	300	ns

Note

1. Measured with a half-sinewave voltage (curve tracer).

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Mounted **without** heatsink compound and 30 ± 5 N force on centre of package.

$T_{mb} < 25$ °C.

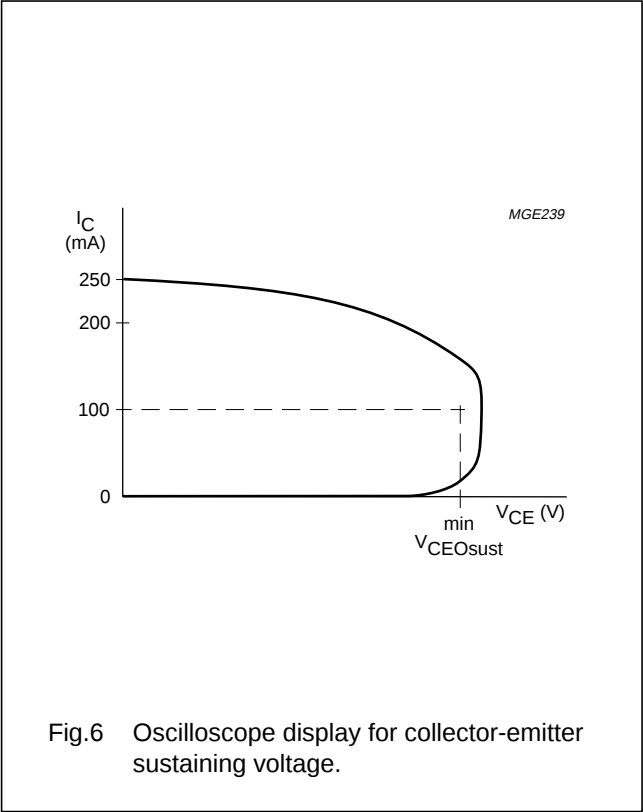
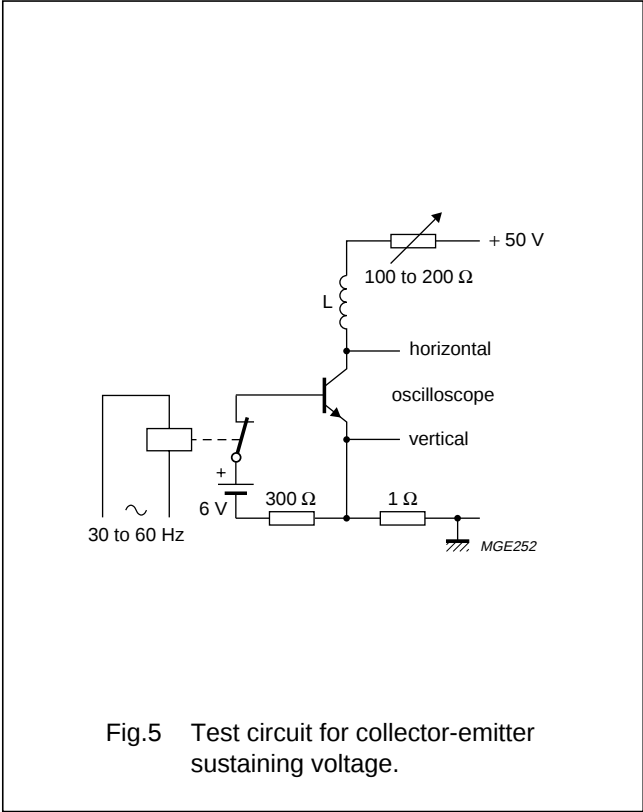
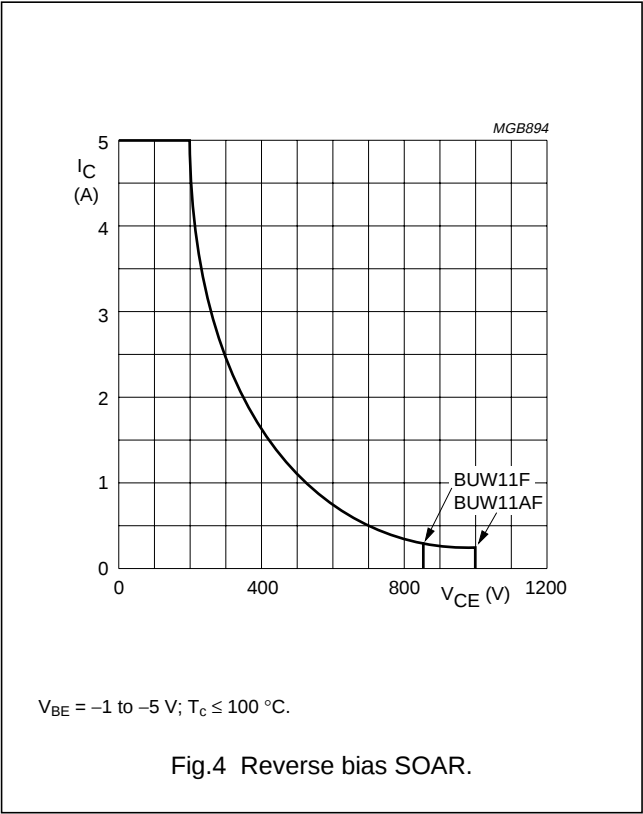
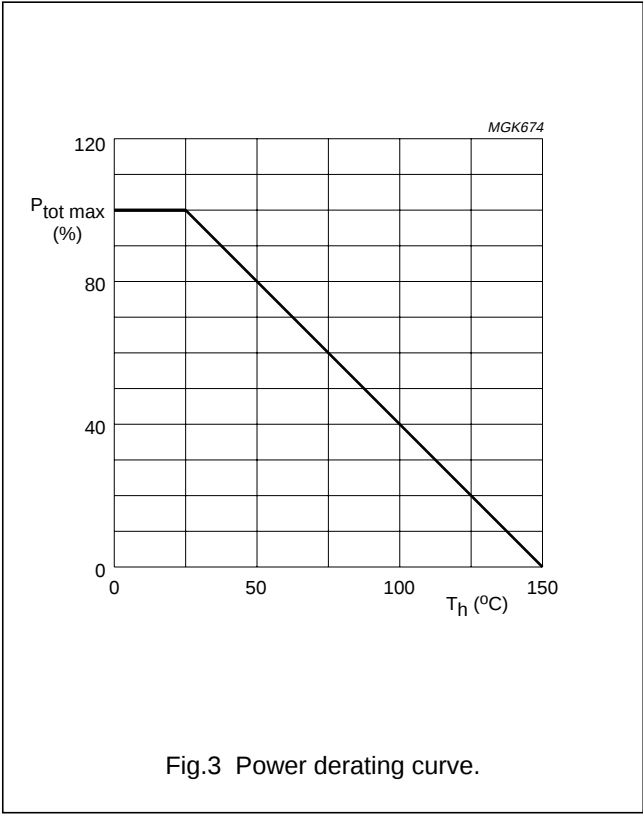
I - Region of permissible DC operation.

II - Permissible extension for repetitive pulse operation.

Fig.2 Forward bias SOAR.

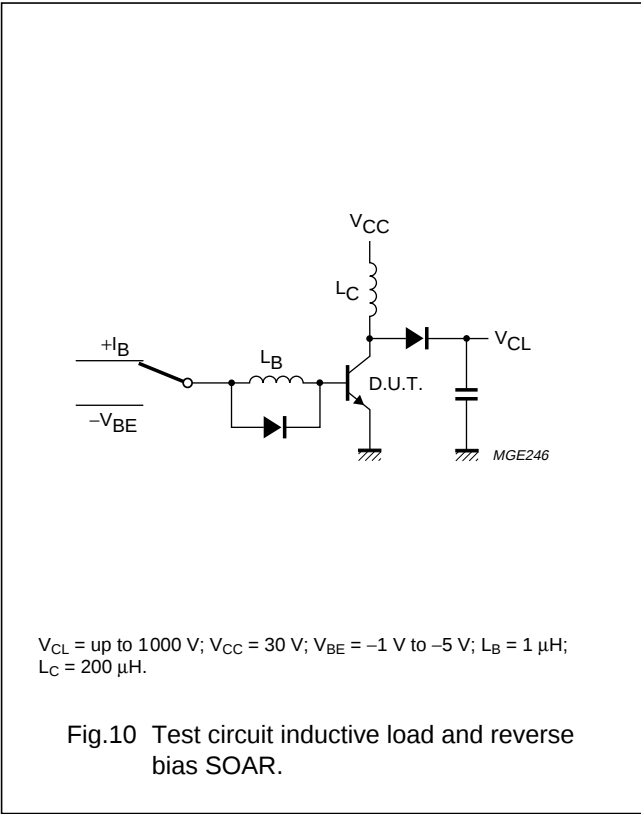
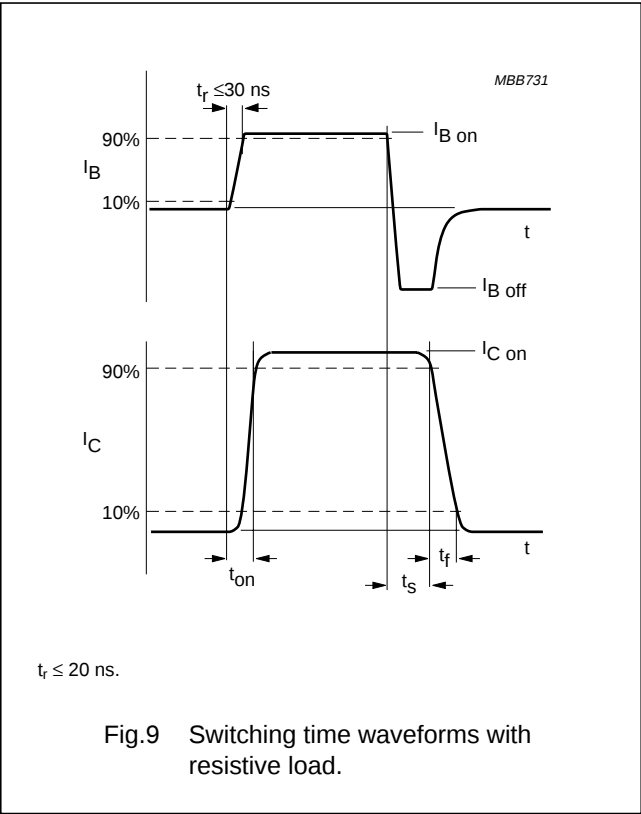
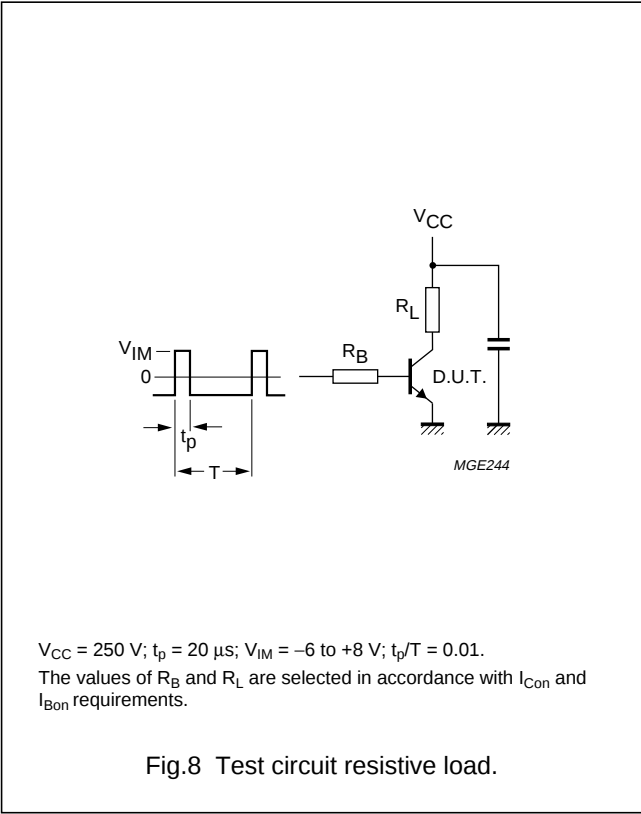
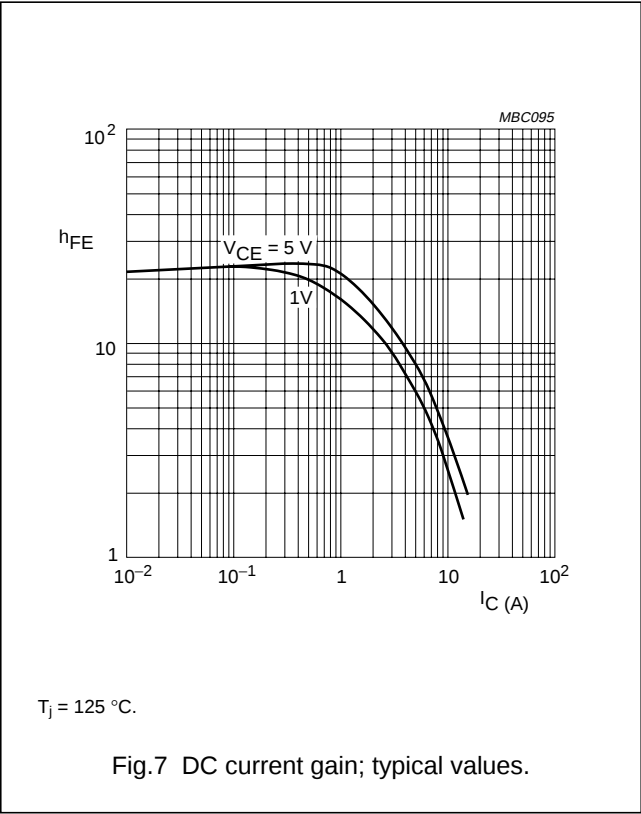
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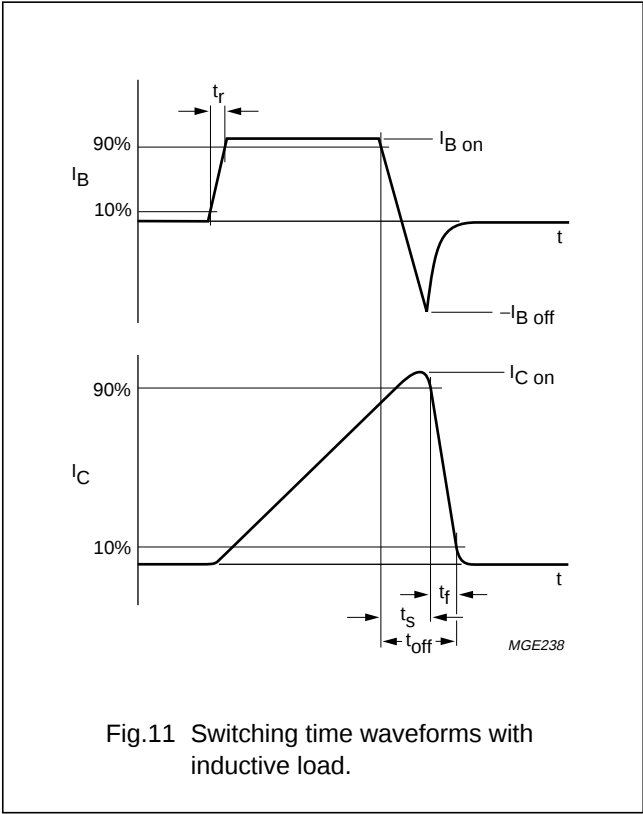
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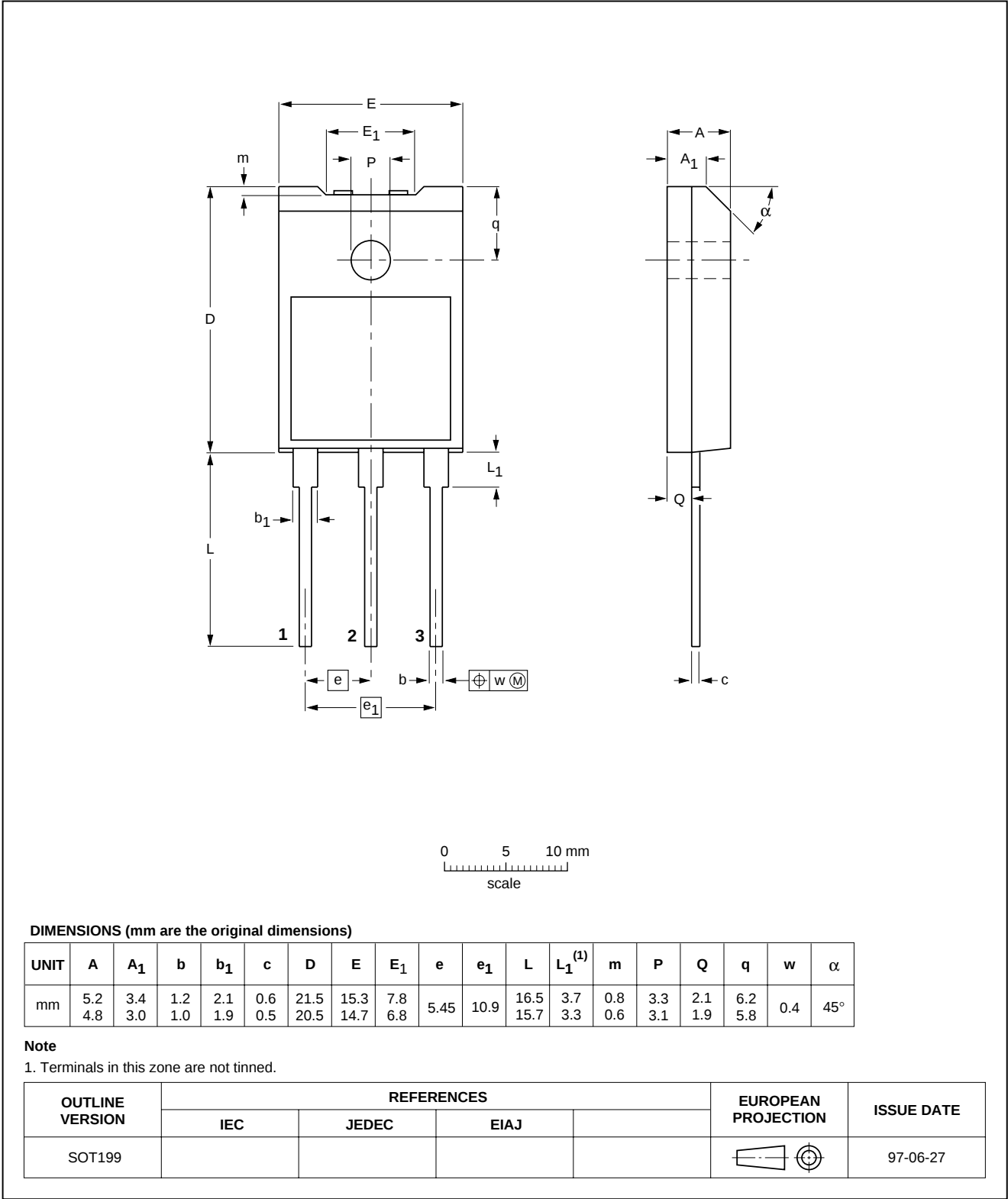
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PACKAGE OUTLINE

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3 leads (in-line)

SOT199



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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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